Amendments to the Claims:

This listing of claims will replace all prior versions, and listings of claims in the application:

Listing of Claims:

1-9. (Canceled)

10. (Currently Amended) A gas supply panel comprising:

a first mass flow controller configured to be in fluid communication with a processing gas source through a first inlet;

a delivery line configured to be in fluid communication with the first mass flow controller and with a processing chamber through a first outlet;

a second mass flow controller configured be in fluid communication with a carrier gas flow and with a source of silicon-containing precursor through a second inlet;

a divert line configured to be in fluid communication with the second mass flow controller and with a chamber exhaust through a second outlet; and

a divert valve configured to selectively place a stabilized flow of the silicon-containing precursor vaporized in the carrier gas from the second mass flow controller in fluid communication with the delivery line or with the divert line.

11. (Original) The gas supply panel of claim 10 wherein the divert valve comprises a three way valve.

12. (Currently Amended) The gas supply panel of claim 10 further comprising a shut off valve in fluid communication with the second mass flow controller and with the ~~second~~ first outlet.

13. (Original) The gas supply panel of claim 10 further comprising a third inlet in fluid communication with the delivery line through a third mass flow controller.

14. (Original) The gas supply panel of claim 10 wherein the silicon-containing precursor comprises a liquid, the gas supply panel further comprising:

an injection valve configured to be in fluid communication with the second inlet

and with the second mass flow controller; and

a third inlet configured to be in fluid communication with a carrier gas source and with the injection valve.

15. (Currently Amended) A substrate processing apparatus comprising:

a processing chamber including an exhaust;

a gas distribution system configured to receive and deliver gases to a gas distribution face plate located proximate to a substrate support within the processing chamber;

a gas supply panel comprising,

a first mass flow controller configured to be in fluid communication with a processing gas source through a first inlet,

a delivery line configured to be in fluid communication with the first mass flow controller and with a first outlet,

a second mass flow controller configured be in fluid communication with a carrier gas and with a source of silicon-containing precursor through a second inlet,

a divert line configured to be in fluid communication with the second mass flow controller and with a second outlet, and

a divert valve configured to selectively place a stabilized flow of the silicon-containing precursor vaporized in the carrier gas from the second mass flow controller in fluid communication with the delivery line or with the divert line;

a first conduit linking the first outlet with the processing chamber; and

a second conduit linking the second outlet with the processing chamber exhaust.

16. (Original) The apparatus of claim 15 wherein the divert valve comprises a three way valve.

17. (Currently Amended) The apparatus of claim 15 further comprising a shut off valve in fluid communication with the second mass flow controller and with the ~~second~~ first outlet.

18. (Original) The apparatus of claim 15 further comprising a third inlet in fluid communication with the delivery line through a third mass flow controller.

19. (Original) The apparatus of claim 15 wherein the silicon-containing precursor comprises a liquid, the gas supply panel further comprising:

an injection valve configured to be in fluid communication with the second inlet and with the second mass flow controller; and

a third inlet configured to be in fluid communication with a carrier gas source and with the injection valve.